

BT1306-400D/600D

Logic level triac

Rev. 01 — 19 February 2004

Product data

1. Product profile

1.1 Description

Logic level sensitive gate triac intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

1.2 Features

- Sensitive gate in all four quadrants
- Low cost package.

1.3 Applications

- General purpose bidirectional switching
- Solid state relays
- Phase control applications
- Low power AC fan speed controllers.

1.4 Quick reference data

- $V_{DRM} \leq 600$ V (BT1306-600D)
- $V_{DRM} \leq 400$ V (BT1306-400D)
- $I_{TSM} \leq 8$ A
- $I_{T(RMS)} \leq 0.6$ A.

2. Pinning information

Table 1: Pinning - SOT54 (TO-92), simplified outline and symbol

Pin	Description	Simplified outline	Symbol
1	main terminal 2		
2	gate		
3	main terminal 1		

MSB033

SOT54 (TO-92)

MBL305



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3. Ordering information

Table 2: Ordering information

Type number	Package		Version
	Name	Description	
BT1306-600D	TO-92	Plastic single-ended leaded (through hole) package; 3 leads	SOT54
BT1306-400D	TO-92	Plastic single-ended leaded (through hole) package; 3 leads	SOT54

4. Limiting values

Table 3: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
V_{DRM}	repetitive peak off-state voltage	$25\text{ °C} \leq T_j \leq 125\text{ °C}$	-	600	V	
				BT1306-600D	400	V
				BT1306-400D		
$I_{\text{T(RMS)}}$	on-state current (RMS value)	full sine wave; $T_{\text{lead}} \leq 65\text{ °C}$; Figure 1 and 2	-	0.6	A	
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_j = 25\text{ °C}$ prior to surge; Figure 3 and 4	-	8	A	
				$t = 20\text{ ms}$	8.8	A
				$t = 16.7\text{ ms}$		
I^2t	I^2t for fusing	$t = 10\text{ ms}$	-	0.32	A^2s	
di_{T}/dt	repetitive rate of rise of on-state current after triggering	$I_{\text{TM}} = 1\text{ A}$; $I_{\text{G}} = 0.2\text{ A}$; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$	-	50	$\text{A}/\mu\text{s}$	
				T2+ G+	50	$\text{A}/\mu\text{s}$
				T2- G-	50	$\text{A}/\mu\text{s}$
				T2- G+	10	$\text{A}/\mu\text{s}$
I_{GM}	gate current (peak value)	$t = 2\text{ }\mu\text{s max}$	-	1	A	
V_{GM}	gate voltage (peak value)		-	5	V	
P_{GM}	gate power (peak value)		-	5	W	
$P_{\text{G(AV)}}$	average gate power	$t = 2\text{ }\mu\text{s max}$; $T_{\text{case}} \leq 80\text{ °C}$	-	0.1	W	
T_{stg}	storage temperature		-40	+150	$^{\circ}\text{C}$	
T_j	junction temperature		-40	+125	$^{\circ}\text{C}$	

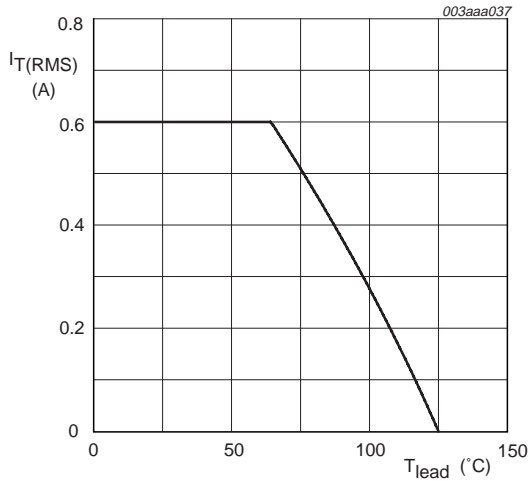
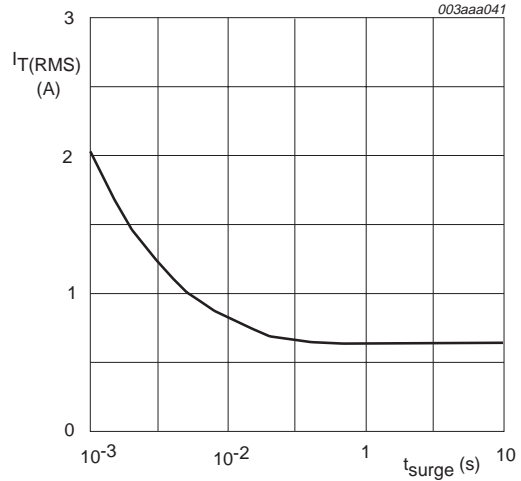
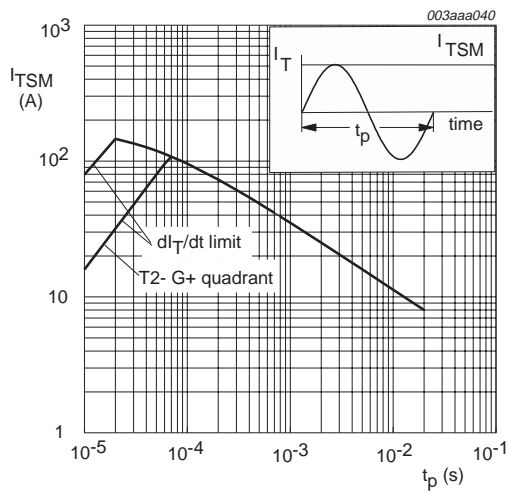


Fig 1. Maximum permissible on-state current (RMS value) as a function of lead temperature.



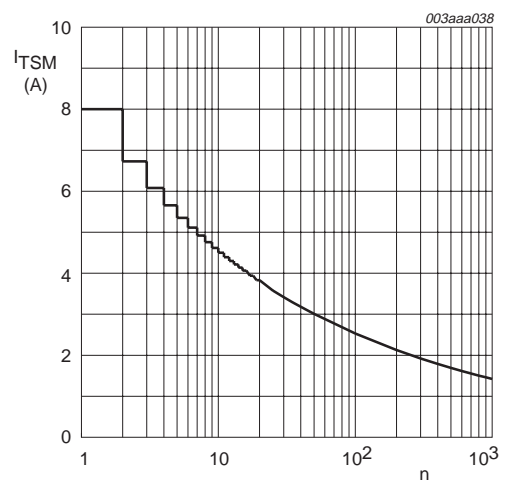
$f = 50 \text{ Hz}$
 $T_{\text{lead}} \leq 65 \text{ }^{\circ}\text{C}$

Fig 2. Maximum permissible repetitive on-state current (RMS value) as a function of surge duration for sinusoidal currents.



$t_p \leq 20 \text{ ms}$
 initial $T_j \leq 25 \text{ }^{\circ}\text{C}$

Fig 3. Maximum permissible non-repetitive peak on-state current as a function of pulse width for sinusoidal currents.



$n = \text{number of cycles}$
 $f = 50 \text{ Hz}$
 initial $T_j \leq 25 \text{ }^{\circ}\text{C}$

Fig 4. Maximum permissible non-repetitive peak on-state current as a function of number of cycles for sinusoidal currents; typical values.

5. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle	-	-	60	K/W
		half cycle			80	
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on a printed-circuit board; lead length = 4 mm; Figure 5	-	150	-	K/W

5.1 Transient thermal impedance

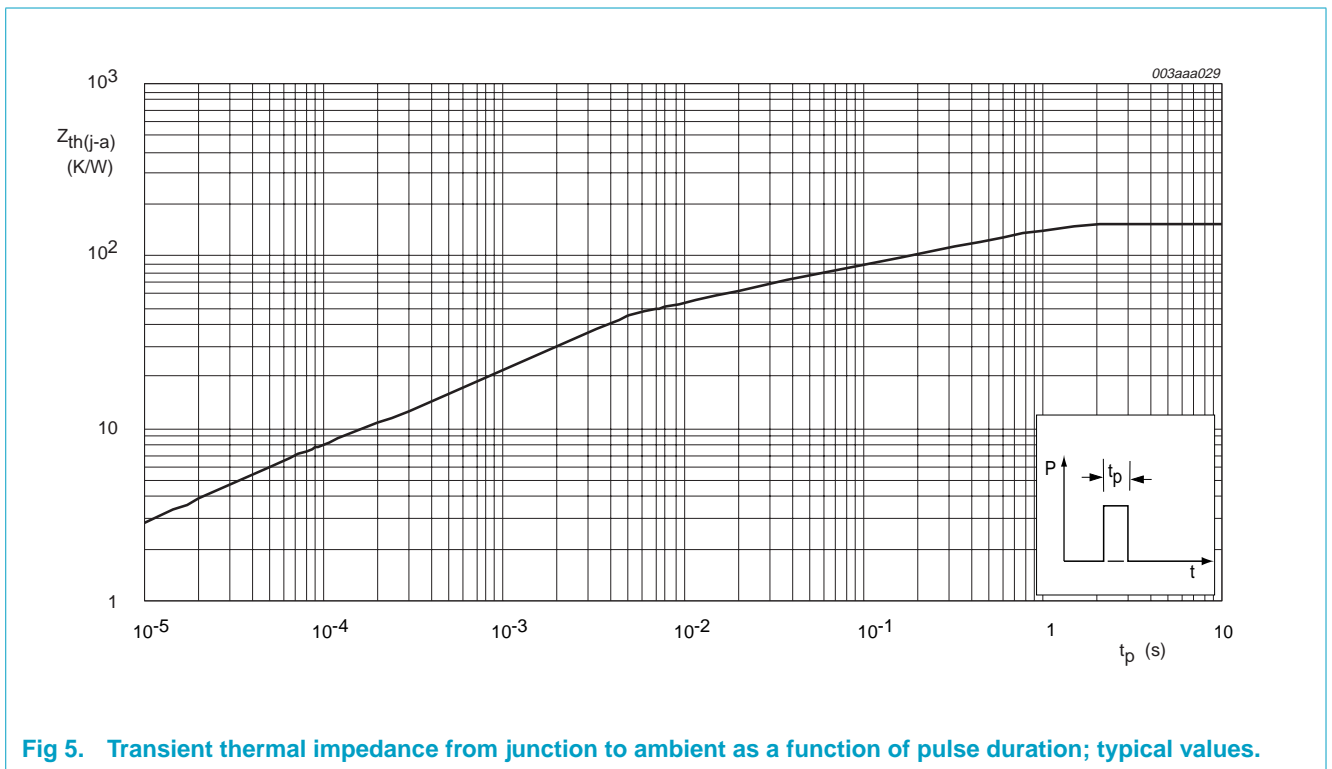


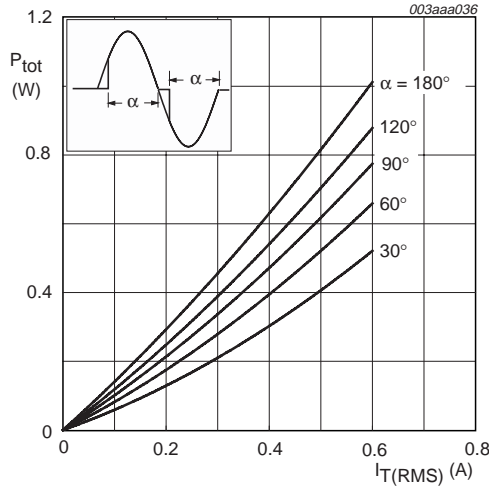
Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values.

6. Characteristics

Table 5: Characteristics

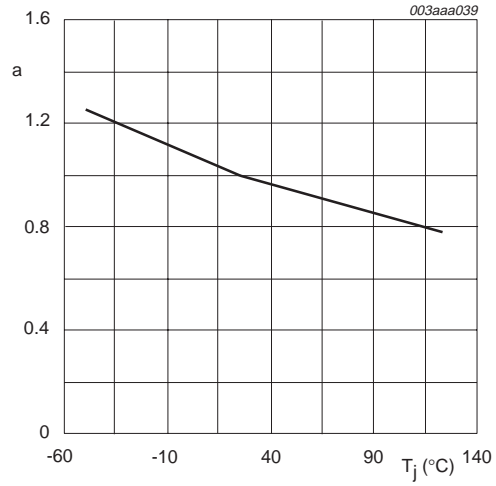
$T_j = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; Figure 8				
		T2+ G+	-	1	5	mA
		T2+ G-	-	2	5	mA
		T2- G-	-	2	5	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; Figure 9				
		T2+ G+	-	1	10	mA
		T2+ G-	-	5	10	mA
		T2- G-	-	1	10	mA
I_H	holding current	$V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$; Figure 10	-	1	10	mA
		$I_T = 0.85\text{ A}$; Figure 11	-	1.4	1.9	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; Figure 7	-	0.9	2	V
		$V_D = V_{DRM}$; $I_T = 0.1\text{ A}$; $T_j = 110\text{ °C}$	0.1	0.7	-	V
I_D	off-state leakage current	$V_D = V_{DRM(max)}$; $T_j = 110\text{ °C}$	-	3	100	μA
Dynamic characteristics						
dV_D/dt	critical rate of rise of off-state voltage	$V_D = 67\%$ of $V_{DM(max)}$; $T_{case} = 110\text{ °C}$; exponential waveform; gate open circuit; Figure 12	30	45	-	$\text{V}/\mu\text{s}$
dV_{com}/dt	critical rate of rise of commutation voltage	$V_D = \text{rated } V_{DM}$; $T_{case} = 50\text{ °C}$; $I_{TM} = 0.84\text{ A}$; commutating $di/dt = 0.3\text{ A/ms}$	-	5	-	$\text{V}/\mu\text{s}$
t_{gt}	gate controlled turn-on time	$I_{TM} = 1.0\text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 25\text{ mA}$; $di_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	μs



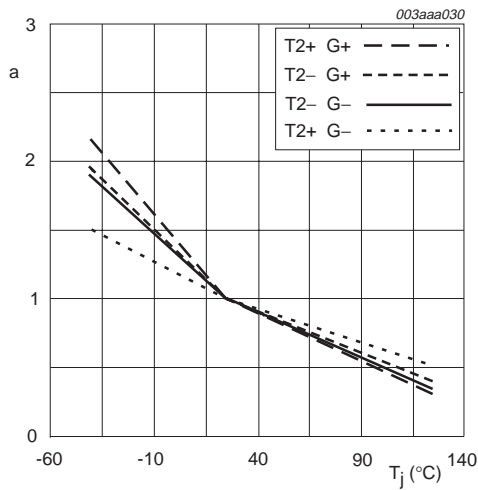
α = conduction angle

Fig 6. On-state dissipation as a function of on-state current (RMS value); maximum values.



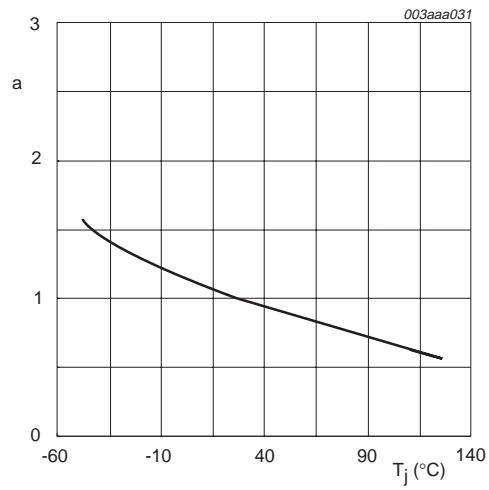
$$a = \frac{V_{GT}(T_j)}{V_{GT}(25^\circ\text{C})}$$

Fig 7. Normalized gate trigger voltage as a function of junction temperature; typical values.



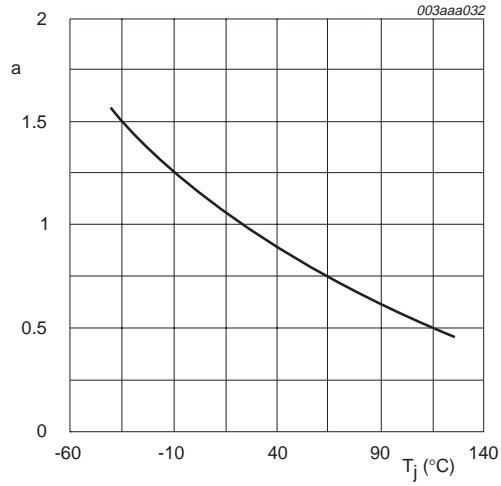
$$a = \frac{I_{GT}(T_j)}{I_{GT}(25^\circ\text{C})}$$

Fig 8. Normalized gate trigger current as a function of junction temperature; typical values.



$$a = \frac{I_L(T_j)}{I_L(25^\circ\text{C})}$$

Fig 9. Normalized latching current as a function of junction temperature; typical values.



$$a = \frac{I_H(T_j)}{I_H(25^\circ\text{C})}$$

Fig 10. Normalized holding current as a function of junction temperature; typical values

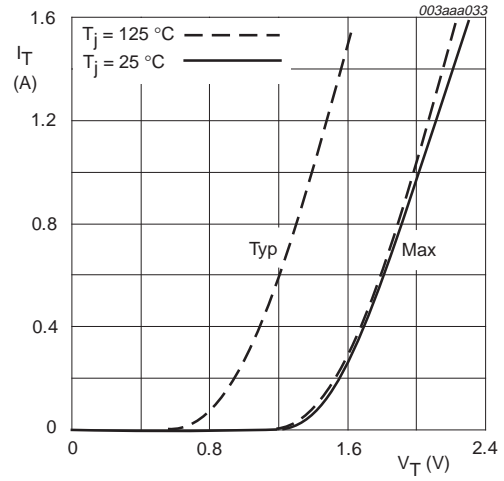


Fig 11. On-state current as a function of on-state voltage; typical and maximum values.

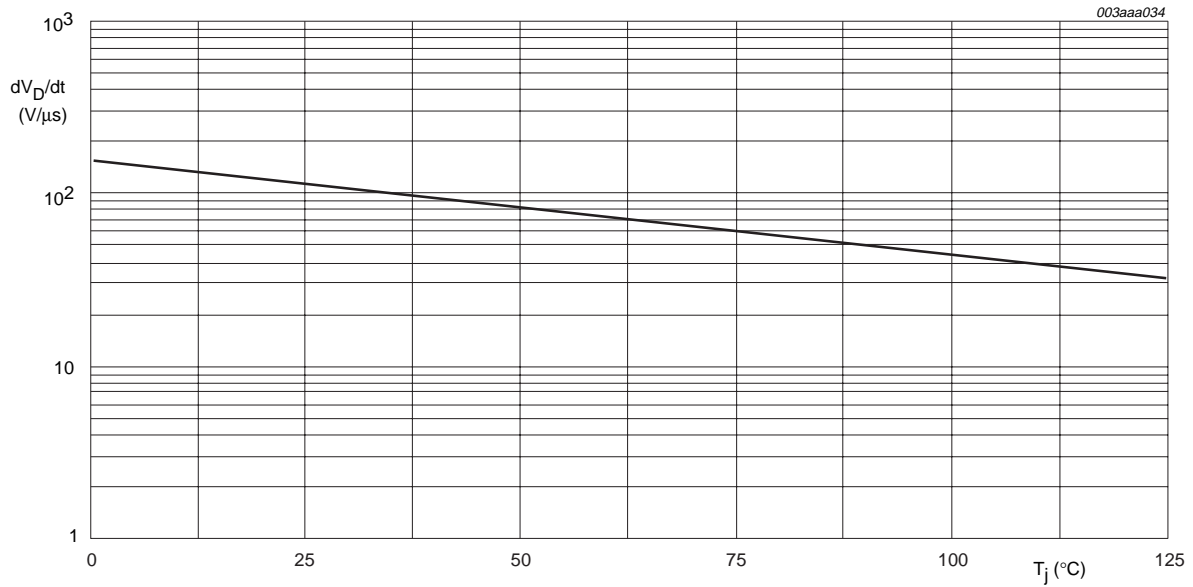


Fig 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values.

7. Package outline

Plastic single-ended leaded (through hole) package; 3 leads

SOT54

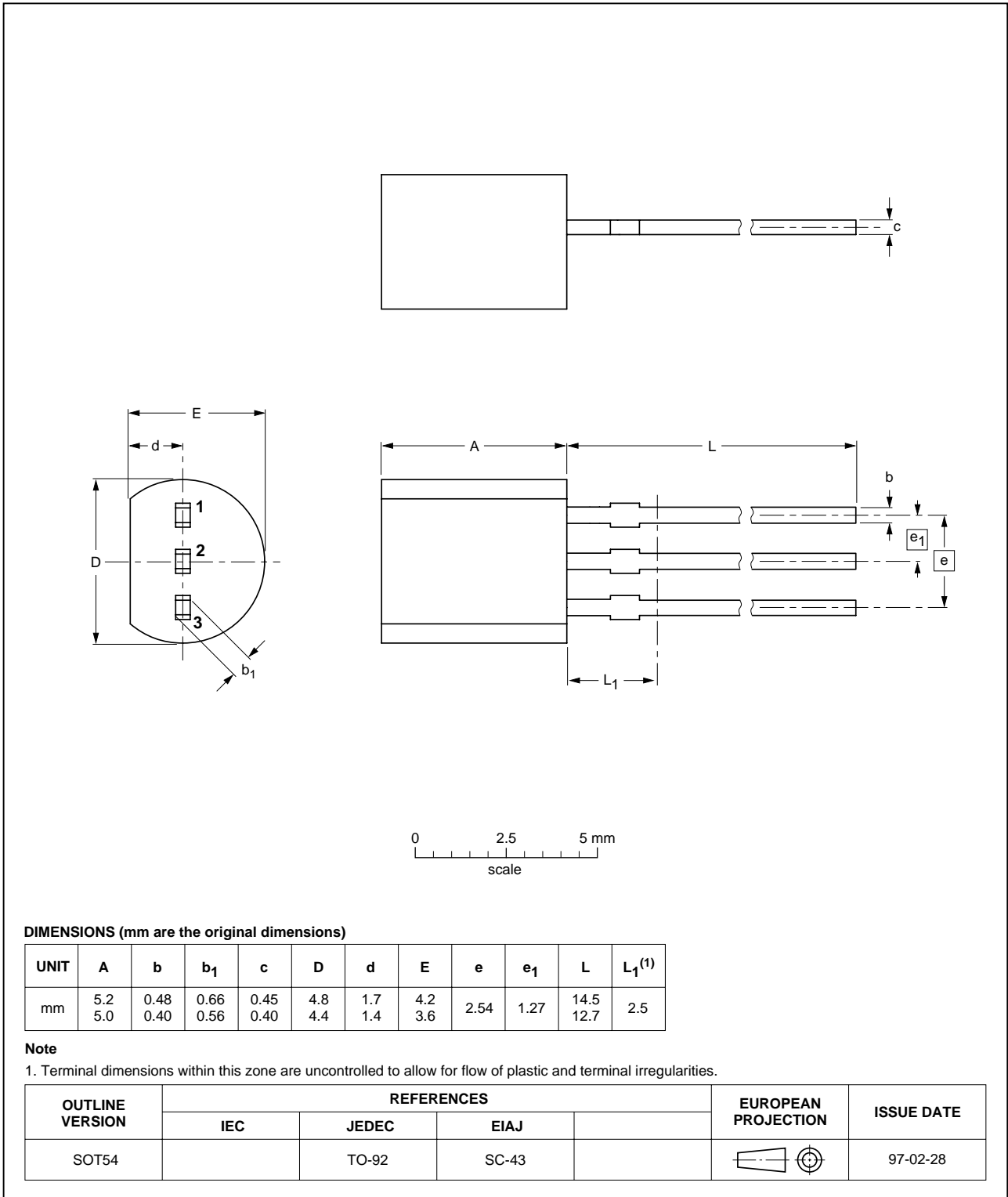


Fig 13. SOT54 (TO-92).

8. Revision history

Table 6: Revision history

Rev	Date	CPCN	Description
01	20040219	-	Product data (9397 750 12593)

9. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2][3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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